

WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:
a first-conductivity type substrate;
5 a first-conductivity type clad layer formed over the substrate;
an active layer formed over the first-conductivity type clad layer;
a second-conductivity type clad layer formed over the
10 active layer while having a ridge spaced apart, at respective opposite longitudinal ends thereof, from a laser emitting end surface and an end surface opposite to the laser emitting end surface by a predetermined gap; and
a current blocking layer formed on the second-
15 conductivity type clad layer around the ridge.

2. The semiconductor laser device according to claim 1, wherein the predetermined gap is 5 μm or more while corresponding to 10% or less of a distance between the laser
20 emitting end surface and the opposite end surface.

3. A method for manufacturing a semiconductor laser device, comprising the steps of:
sequentially forming over at least a first-
25 conductivity type clad layer, an active layer and a second-

conductivity type clad layer over a substrate;

forming, on the second-conductivity type clad layer, a mask adapted to form a ridge such that the ridge is spaced apart, at respective opposite longitudinal ends thereof, from a laser emitting end surface and an end surface opposite to the laser emitting end surface by a predetermined gap;

etching the second-conductivity type clad layer to a predetermined depth by use of the mask, thereby forming the ridge; and

forming a current blocking layer made of a first-conductivity type semiconductor material on the etched second-conductivity type clad layer around the ridge.

4. The method according to claim 3, wherein the predetermined gap is 5 μm or more while corresponding to 10% or less of a distance between the laser emitting end surface and the opposite end surface.

5. The method according to claim 3, wherein the step of forming the ridge comprises the steps of:

forming a ridge structure in accordance with a dry etching process; and

removing defects formed on a surface of the ridge structure in accordance with a wet etching process, thereby forming the ridge.